

FC809

Silicon Barrier Diode

# 30V, 70mA Rectifier

### **Applications**

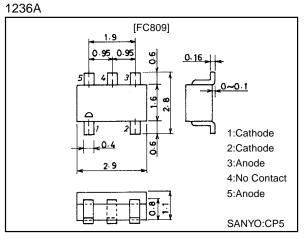
- · General rectification applications.
- High frequency rectification (switching regulators, converters, choppers).

### **Features**

- · Low forward voltage ( $V_F$  max=0.55V).
- $\cdot$  Fast reverse recovery time (trr max=10ns).
- Composite type with 2 diodes contained in the CP package currently in use, saving the mounting space greatly.
- The FC809 is formed with two chips, each being equivalent to the SB007-03CP, placed in one package.

## **Package Dimensions**

unit:mm



# **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C (Value per element)

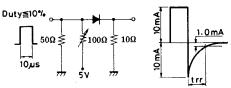
| Parameter                                | Symbol           | Conditions              | Ratings     | Unit |
|--|------------------|-------------------------|-------------|------|
| Repetitive Peak Reverse Voltage          | VRRM             |                         | 30          | V    |
| Nonrepetitive Peak Reverse Surge Voltage | V <sub>RSM</sub> |                         | 35          | V    |
| Average Output Current                   | lo               |                         | 70          | mA   |
| Surge Forward Current                    | IFSM             | 50Hz sine wave, 1 cycle | 2           | A    |
| Junction Temperature                     | Tj               |                         | -55 to +125 | °C   |
| Storage Temperature                      | Tstg             |                         | -55 to +125 | °C   |

### Electrical Characteristics at Ta = 25°C (Value per element)

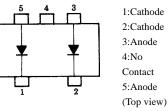
| .Parameter               | Symbol         | Conditions                             | Ratings |     |      | Unit |
|--------------------------|----------------|--|---------|-----|------|------|
|                          | Symbol         |  | min     | typ | max  |      |
| Reverse Voltage          | VR             | I <sub>R</sub> =20μΑ                   | 30      |     |      | V    |
| Forward Voltage          | VF             | I <sub>F</sub> =70mA                   |         |     | 0.55 | V    |
| Reverse Current          | I <sub>R</sub> | V <sub>R</sub> =15V                    |         |     | 5.0  | μA   |
| Interteminal Capacitance | С              | V <sub>R</sub> =10V, f=1MHz            |         | 3.0 |      | pF   |
| Reverse Recovery Time    | trr            | IF=IR=10mA, See specified Test Circuit |         |     | 10   | ns   |
| Thermal Resistance       | Rth (j-a)      |  |         | 560 |      | °C/W |

· Marking:809

#### trr Test Circuit

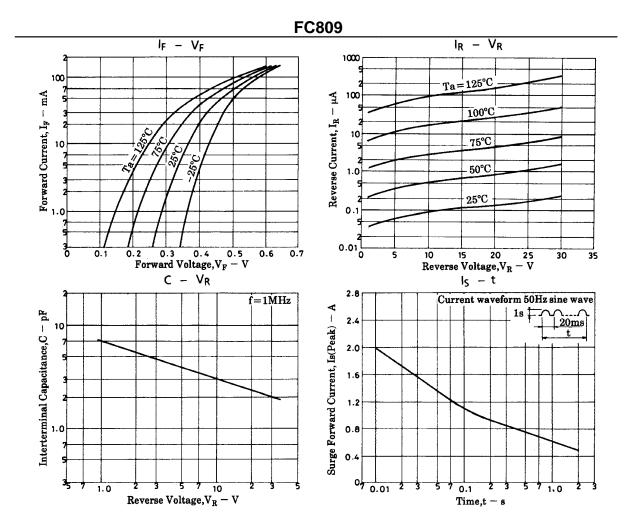


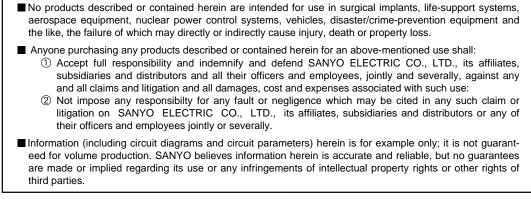
### **Electrical Connection**



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This catalog provides information as of February, 1998. Specifications and information herein are subject to change without notice.